

**DECLARATION AND POWER OF ATTORNEY  
FOR U.S. REISSUE PATENT APPLICATION**

Original    Supplemental    Substitute    PCT    Design

As a below named inventor, I hereby declare that: my residence, post office address and citizenship are as stated below next to my name; that I verily believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural inventors are named below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

**TITLE: METHOD FOR FABRICATING MOS SEMICONDUCTOR DEVICE HAVING SALICIDE REGION AND LDD STRUCTURE**

of which is described and claimed in:

- the attached specification (copy of U.S. Patent No. 6,255,181) AND the attached amendment, or  
 the specification in the application Serial No. \_\_\_\_\_ filed \_\_\_\_\_,  
and with amendments through \_\_\_\_\_ (if applicable), or

I hereby state that I have reviewed and understand the content of the above-identified specification, including the claims, as amended by any amendment(s) referred to above.

I acknowledge my duty to disclose information of which I am aware which is material to the examination of this application in accordance with Title 37, Code of Federal Regulations, §1.56(a).

I hereby claim foreign priority benefits under Title 35, United States Code, §119 (and §172 if this application is for a Design) of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application n which priority is claimed:

COUNTRY	APPLICATION NO.	DATE OF FILING	PRIORITY CLAIMED
Republic of Korea	97-50829	October 1, 1997	Yes

I hereby claim the benefit under Title 35, United States code, §120 and §119(e) of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, §112, I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal Regulations, §1.56(a) which occurred between the filing date of the prior application and the national or PCT international filing date of this application:

APPLICATION SERIAL NO.	U.S. FILING DATE	STATUS: PATENTED, PENDING, ABANDONED

And I hereby appoint Adam C. Valentine, Reg. No. 33289 and William S. Francos, Reg. No. 38,456, and the firm of **VOLENTINE FRANCOS, P.L.L.C.**, jointly and severally, attorneys to prosecute this application and to transact all business in the U.S. Patent and Trademark Office connected therewith.

I hereby authorize the U.S. attorneys named herein to accept and follow instructions from **Samsung Electronics Co., Ltd** as to any action to be taken in the U.S. Patent and Trademark Office regarding this application without direct communication between the U.S. attorneys and myself. In the event of a change in the persons from whom instructions may be taken, the U.S. attorneys named herein will be so notified by me.

*Kindly direct all correspondence to:*

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**REISSUE ERROR**

*I hereby declare as follows:*

- (1) This is a reissue application of U.S. Patent No. 6,255,181 B1 (hereinbelow the '181 patent), issued July 3, 2001.
- (2) I believe the '181 patent to be wholly or partly inoperative by reason of the patentee claiming less than the patentee had a right to claim.
- (3) The original application (Serial No. 09/161,979, filed September 29, 1998) of the '181 patent included a single claim ("claim 9") directed to the third embodiment of the invention, which is shown in FIGS. 3A-3F of the '181 patent.

(4) In an Office Action dated October 6, 1999, claim 9 of the original application was rejected under 35 U.S.C. ¶102(b) as being unpatentable over Fulford, Jr. et al. (U.S. Patent No. 5,923,983).

(5) In an Amendment dated December 9, 1999, claim 9 of the original application was canceled without prejudice.

(6) The cancellation of claim 9 of the original application was in error. Instead, claim 9 should have been amended to clarify that the "buffering layer" (35 of FIG. 3B) is "deposited over" the semiconductor substrate (31) having the gate pattern (32, 33) and lightly doped regions (34). Also, in addition to amending claim 9, dependent claims should have been added to define the buffering layer as either SiO<sub>2</sub> or SiN, to define the thickness of the buffering layer as about 30Å or more, and to define the transition metal as Co, Ti and/or Ni. Such an amended claim 9 and new dependent claims would have overcome the rejection under 35 U.S.C. ¶102(b) since Fulford, Jr. et al. relies on oxidation of underlying silicon-containing layers to form a polycrystalline oxide 24, since Fulford, Jr. et al. does not quantify the thickness of the polycrystalline oxide 24, and since Fulford, Jr. et al. does not specify the materials for formation of a silicide. Also, it is believed that the last two steps of claim 9 are not necessary to define over the prior art, and accordingly, to adequately claim the third embodiment of the invention, an additional set of claims should have been added which do not require the formation of a transition metal and subsequent anneal.

(7) To correct the error described in paragraph (6), the amendment submitted herewith adds new claims 9-17. New independent claim 9 is the same as the claim 9 of the original application, except that the phrase "forming a buffering layer on" has been changed to -- depositing a buffering layer over -. New dependent claim 10 recites the buffering layer as being SiO<sub>2</sub>, new dependent claim 11 recites the buffering layer as being SiN, new dependent claim 12 recites the thickness of the buffering layer as about 30Å or more, and new dependent claim 13 recites the transition metal as Co, Ti and/or Ni. New independent claim 14 is the same as new independent claim 9, except that the last two steps of claim 9 do not appear in claim 14. New dependent claim 15 recites the buffering layer as being SiO<sub>2</sub>, new dependent claim 16 recites the buffering layer as being SiN, and new dependent claim 17 recites the thickness of the buffering layer as about 30Å or more.

(8) Support for depositing a SiO<sub>2</sub> or SiN buffering layer at a thickness of about 30Å or more over the substrate (as recited in new claims 9-12 and 14-16) and can be found at least at column 5, lines 16-23, of the '181 patent. Support for a transition metal of Co, Ti and/or Ni (as recited in new claims 13 and 17) can be found at least at column 5, lines 46-48, of the '181 patent. No new matter has been added.

(9) All errors described herein and being corrected by this reissue application occurred without deceptive intention.

I further declare that all statements made herein of my own knowledge are true, and that all statements on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

1<sup>st</sup> Inventor Yong-Hyung OH-SUNG SONG Date: June 25, 2003  
Oh-Sung SONG

2<sup>nd</sup> Inventor Ja-Hum Ku Date: June 25, 2003  
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